

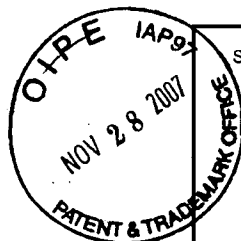


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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known		
			Application Number	10/581,797 – Conf. # 4944	
			Filing Date	June 2, 2006	
			First Named Inventor	Yang Yang	
			Art Unit	2818	
			Examiner Name	Long K. Tran	
Sheet	1	of	6	Attorney Docket Number	58086-231274

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
/LT/	A1	2002/0010261 A1	01-24-2002	Callahan et al.	
	A2	2002/0163828 A1	11-07-2002	Krieger et al.	
	A3	2002/0163831 A1	11-07-2002	Krieger et al.	
	A4	2002/0195600 A1	12-26-2002	Leuschner	
	A5	2003/0053350 A1	03-20-2003	Krieger et al.	
	A6	2003/0063362 A1	04-03-2003	Demir et al.	
	A7	2003/0155602 A1	08-21-2003	Krieger et al.	
	A8	2003/0173612 A1	09-18-2003	Krieger et al.	
	A9	2003/0178667 A1	09-25-2003	Krieger et al.	
	A10	2003/0179633 A1	09-25-2003	Krieger et al.	
	A11	2004/0026714 A1	02-12-2004	Krieger et al.	
	A12	2004/0159835 A1	08-19-2004	Krieger et al.	
	A13	2004/0160801 A1	08-19-2004	Krieger et al.	
	A14	2004/0246768 A1	12-09-2004	Krieger et al.	
	A15	2005/0111071 A1	05-26-2005	Kojima et al.	
	A16	3719933	03-06-1973	Wakabayashi et al.	
	A17	3833894	09-03-1974	Aviram et al.	
	A18	4144418	03-13-1979	Girard et al.	
	A19	4371883	02-01-1983	Potember et al.	
	A20	4652894	03-24-1987	Potember et al.	
	A21	4663270	05-05-1987	Potember et al.	
	A22	4987023	01-22-1991	Sato et al.	
	A23	5075738	12-24-1991	Matsuda et al.	
	A24	5136212	08-04-1992	Eguchi et al.	
	A25	5238607	08-24-1993	Herron et al.	
	A26	5543631	08-06-1996	Weinberger	
	A27	5563424	10-08-1996	Yang et al.	
	A28	5569565	10-29-1996	Kawakami et al.	
	A29	5610898	03-11-1997	Takimoto et al.	
	A30	5761115	06-02-1998	Kozicki et al.	
	A31	6015631	01-18-2000	Park	
	A32	6055180	04-25-2000	Gudesen, et al.	
	A33	6122031	09-19-2000	Terada et al.	
	A34	6208553	03-27-2001	Gryko et al.	
	A35	6229047	05-08-2001	Glaser et al.	
	A36	6631085	10-07-2003	Kleveland et al.	
	A37	6774880	08-10-2004	Kobayashi	
	A38	6828685	12-04-2004	Stasiak	
	A39	6852555	02-08-2005	Roman et al.	

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FOREIGN PATENT DOCUMENTS						
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
/LT/	B1	WO 01/71814 A1	09-27-2001	Japan Science and Technology Corporation		
	B2	WO 02/37500 A1	05-10-2002	The Regents of the University of California		
	B3	WO 02/091496 A2	11-14-2002	Coatue Corporation		
/LT/	B4	WO 2004/064074	07-29-04	Siemens Aktiengesellschaft		

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NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
/LT/	C1	The Electrochemical Society - Current Affairs - Abstracts of "Recent News" Papers, Presented at Electronics Division Semiconductor Symposia, Los Angeles, CA (1962).		
	C2	OVSHINSKY, S.R., "Localized States in the Gap of Amorphous Semiconductors", Phys. Rev. Lett., Vol. 36 (No. 24), June 14, 1976, p. 1469-1472.		
	C3	HOVEL, H.J. and J.J. URGELL, "Switching and Memory Characteristics of ZnSe – Ge Heterojunctions", J. Appl. Phys. 42, 5076 (1971).		
	C4	KUMAI, R., Y. OKIMOTO and Y. TOKURA, "Current-Induced Insulator-Metal Transition and Pattern Formation in an Organic Charge-Transfer Complex", Science 284, 1645 (1999).		
	C5	GARNIER, F., R. HAJLAOUI, A. YASSAR and P. SHIRAKAWA, "All-Polymer Field-Effect Transistor Realized by Printing Techniques", Science 265, 1684 (1994).		
	C6	HIDE, F., M.A. DIAZ-GARCIA, B.J. SCHWARTZ, M.R.A. ANDERSSON, Q. PEI and A.J. HEEGER, Science 273, 1833 (1996).		
	C7	FUJITA, W. and K. AWAGA, "Room-Temperature Magnetic Bistability in Organic Radical Crystals", Science, Vol. 286 p. 261 (1999).		
	C8	BURROUGHES, J.H., D.D.C. BRADLEY, A.R. BROWN, R.N. MARKS, K. MACKAY, R.H. FRIEND, P.L. BURN and A.B. HOLMES, "Light-Emitting Diodes Based on Conjugated Polymers", Nature, Vol. 347, p. 539 (1990).		
	C9	YAMADA, T., D. ZOU, H. JEONG, Y. AKAKI and T. TSUTSUI, "Recoverable Degradation and Internal Field Forming Process Accompanied by the Orientation of Dipoles in Organic Light Emitting Diodes", Synthetic Metals, 111-112, 237 (2000).		
	C10	LIU, J., Y. SHI, L.P. MA and Y. YANG, "Device Performance and Polymer Morphology in Polymer Light Emitting Diodes: The Control of Device Electrical Properties and Metal/Polymer Contact", J. Appl. Phys. 88, 605 (2000).		
	C11	HAMADA, Y., C. ADACHI, T. TSUTSUI and S. SAITO, "Blue-Light-Emitting Organic Electroluminescent Devices with Oxadiazole Dimer Dyes as an Emitter", Jpn. J. Appl. Phys. 31, 1812 (1992).		
/LT/	C12	SILVA, et al., Bistable Switching And Memory Devices; Journal of non-Crystalline Solids; (1970) oo. 316-333 No. Holland Publishing Co., Amsterdam		

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/LT/	C13	BOZANO, et al; Mechanism for Bistability in Organic Memory Elements; Applied Physics Letters, (2004); Vol. 84, No. 4, pp. 607-609; 2004 American Institute of Physics.	
	C14	HUA, et al.; New Organic Bistable Films for Ultrafast Electric Memories; Applied Surface Science, 169-170 (2001) pp. 447-451, Elsevier Science B.V.	
	C15	BEINHOFF, et al., Polybiphenylmethylenes: New Polymers for Bistable Organic Switches; Polymeric Materials: Science and Engineering 90, (2004) 211, 212, U.S.	
	C16	SEZI, et al.; Organic Materials for High-Density NonVolatile Memory Applications; Proc. IEEE Int. Elec. Dev. Meeting; (2003); Germany	
	C17	KEVORKIAN, et al.; bistable Switching in Organic Thin Films; Discussions of the Faraday Society, 51, (1971) pp. 139-142; U.S.	
	C18	PEI, Qibing et al., Polymer Light-Emitting Electrochemical Cells, Science, New Series, Vol. 269, No. 5227 (August 25, 1995), pp. 1086-1088	
	C19	Kolega et al., Langmuir 1998, vol. 14, p. 5469-5478.	
	C20	Schlaf et al., "Photoemission Spectroscopy of LiF Coated Al and Pt Electrodes", Journal of Applied Physics, Vol. 84, No. 12, pgs. 6729-6736. (1998)	
	C21	BEELER, F., O.K. ANDERSEN and M. SCHEFFLER", Theoretical Evidence for Low-Spin Ground States of Early Interstitial and Late Substitutional 3d Transition-Metal Ions in Silicon", Phys. Rev. Lett. 55, 1498 (1985).	
	C22	BOYD, G.D., J. CHENG and P.D.T. NGO, "Liquid-Crystal Orientational Bistability and Nematic Storage Effects", Appl. Phys., Lett. 36, 556 (1980).	
	C23	BROWN, W.D. and J.E. BREWER, "Nonvolatile Semiconductor Memory Technology", IEEE Press, New York (1998).	
	C24	CHEN, J., W. WANG, M.A. REED, A.M. RAWLETT, D.W. PRICE and J.M. TOUR, "Room-Temperature Negative Differential Resistance in Nanoscale Molecular Junctions", Appl. Phys. Lett. 77, 1224 (2000).	
	C25	DEWALD, J.F., A.D. PEARSON, W.R. NORTHOVER and W.F. PECK, JR., "Semi-Conducting Glasses", Electrochem. Soc., 109, 243c (1962).	
	C26	FALTERMEIER, C., C. GOLDBERG, M. JONES, A. UPHAM, D. MANGER, G. PETERSON, J. LAU, A.E. KALOYEROS, B. ARKLES, and A. PARANJPE, "Barrier Properties of Titanium Nitride Films Grown by Low Temperature Chemical Vapor Deposition from Titanium Tetraoxide", J. Electrochemical Society, 144, 1002 (1997).	
	C27	GRULER, H. and L. CHEUNG, "Dielectric Alignment in an Electrically Conducting Nematic Liquid Crystal", J. Appl. Phys. 46, 5097 (1975).	
	C28	ISTRATOV, A.A. and E.R. WEBER, "Physics of Copper in Silicon", J. Electrochemical Society, 149, G21 (2002).	
	C29	ISTRATOV, A.A., C. FLINK, H. HIESLMAIR, E.R. WEBER and T. HEISER, "Intrinsic Diffusion Coefficient of Interstitial Copper in Silicon", Phys. Rev. Lett. 81, 1243 (1998).	
	C30	ISTRATOV, A.A., C. FLINK, H. HIESLMAIR, S.A. MCHUGO and E.R. WEBER, "Diffusion, Solubility and Gettering of Copper in Silicon", Materials Science and Engineering Technology B, 72, 99 (2000).	
	C31	KALOYEROS, A.E. and E. EISENBRAUN, "Ultrathin Diffusion Barriers/Liners for Gigascale Copper Metallization", Annual Rev. Materials Science, 30, 363 (2000).	
	C32	KRISHNAMOORTHY, A., K. CHANDA, S.P. MURARKA, G. RAMANATH and J.G. RYAN, "Self-Assembled Near-Zero-Thickness Molecular Layers as Diffusion Barriers for Cu Metallization", Appl. Phys. Lett. 78, 2467 (2001).	
/LT/	C33	LANE, M.W., E.G. LINIGER and J.R. LLOYD, "Relationship Between Interfacial Adhesion and Electromigration in Cu Metallization", J. Appl. Phys. 93, 1417 (2003).	

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Sheet	4	of	6	Attorney Docket Number	58086-231274

/LT/	C34	LEE, K.L., C.K. HU and K.N. TU, "In-Situ Scanning Electron Microscope Comparison Studies on Electromigration of Cu and Cu(Sn) Alloys for Advanced Chip Interconnects", J. Appl. Phys. 78, 4428-4437 (1995).	
	C35	LOKE, A.L.S., J.T. WETZEL, P.H. TOWNSEND, T. TANABE, R.N. VRTIS, M.P. ZUSSMAN, D. KUMAR, C. RYU and S.S. WONG, "Kinetics of Copper Drift in Low-Kappa Polymer Interlevel Dielectrics", IEEE Transactions on Electron Devices 46, 2178 (1999).	
	C36	MA, L.P., J. LIU, S.M. PYO, Q.F. XU and Y. YANG, "Organic Bistable Devices", Mol. Cryst. Liq. Cryst. 378, 185 (2002).	
	C37	MA, L.P., W.J. YANG, S.S. XIE and S.J. PANG, "Ultrahigh Density Data Storage from Local Polymerization by a Scanning Tunneling Microscope", Appl. Phys. Lett. 73, 3303 (1998).	
	C38	MCBRAYER, J.D., R.M. SWANSON and T.W. SIGMON, "Diffusion of Metals in Silicon Dioxide", J. Electrochem. Soc. 133, 1242 (1986).	
	C39	NAKAYAMA, K., K. KOJIMA, Y. IMAI, T. KASAI, S. FUKUSHIMA, A. KITAGAWA, M. KUMEDA, Y. KAKIMOTO and M. SUZUKI, "Nonvolatile Memory Based on Phase Change in Se-Sb-Te Glass", J. J. Appl. Phys., Part 1, 42 (2A), 404 (2003).	
	C40	OSTRAAT, M.L., J.W. DE BLAUWE, M.L. GREEN, L.D. BELL, M.L. BRONGERMA, J.R. CASPERSON, C. FLAGAN and H.A. ATWATER, "Synthesis and Characterization of Aerosol Silicon Nanocrystal Nonvolatile Floating-Gate Memory Devices", Appl. Phys. Lett. 79, 433 (2001).	
	C41	PATEL, J.S., "Room-Temperature Switching Behavior of Ferroelectric Liquid Crystals in Thin Cells", Appl. Phys. Lett. 47, 1277 (1985).	
	C42	ROSENBERG, R., D.C. EDELSTEIN, C.K. HU, and K.P. RODBELL, "Copper Metallization for High Performance Silicon Technology", Annual Rev. Materials Science, 30, 229 (2000).	
	C43	SEGUI, Y., Ai BUI and H. CARCHANO, "Switching in Polystyrene Films: Transition from On to Off State", J. Appl. Phys. 47, 140 (1976).	
	C44	SPRANG, H. A. van, and J.L. M. van de VENNE, "Influence of the Surface Interaction on Threshold Values in the Cholestericnematic Phase Transition", J. Appl. Phys. 57, 175 (1985).	
	C45	WANG, M.T., Y.C. LIN, and M.C. CHEN, "Barrier Properties of Very Thin Ta and TaN layers Against Copper Diffusion", J. Electrochemical Society, 145, 2538 (1998).	
	C46	YANG, K.H., T.C. CHIEU and S. OSOFSKY, "Depolarization Field and Ionic Effects on the Bistability of Surface-Stabilized Ferroelectric Liquid-Crystal Devices", Appl. Phys. Lett. 55, 125 (1989).	
	C47	Bachtold, Adrian et al., "Logic Circuits with Carbon Nanotube Transistors", <u>SCIENCE</u> , Vol. 294, November 9, 2001, pps. 1317-1320.	
	C48	Duan, Xiangfeng et al., "Indium Phosphide Nanowires as Building Blocks for Nanoscale Electronic and Optoelectronic Devices", <u>NATURE</u> , Vol. 49, January 4, 2001, pps. 66-69.	
	C49	Gudiksen, Mark S. et al., "Growth of Nanowire Superlattice Structures for Nanoscale Photonics and Electronics", <u>NATURE</u> , Vol. 415, February 7, 2002, pps. 617-620.	
	C50	Huynh, Wendy U. et al., "Hybrid Nanorod-Polymer Solar Cells", <u>SCIENCE</u> , Vol. 295, March 29, 2002, pps. 2425-2427.	
	C51	Adams, David M. et al., "Charge Transfer on the Nanoscale: Current Status", <u>J. Phys. Chem. B</u> , 2003, Vol. 107, No. 28, pps. 6668-6697.	
	C52	Kamat, Prashant V. et al., "Electrochemical Modulation of Fluorophore Emission on a Nanostructured Gold Film", <u>Angew. Chem. Int. Ed.</u> 2002, Vol. 41, No. 15, pps. 2764-2767.	
✓	C53	Chen, Shaowei et al., "Gold Nanoelectrodes of Varied Size: Transition to Molecule-Like Charging", <u>SCIENCE</u> , Vol. 280, June 26, 1998, pps. 2098-2101.	
/LT/	C54	Wuelfing, W. Peter et al., "Electronic Conductivity of Solid-State, Mixed-Valent, Monolayer-Protected Au Clusters", <u>J. Am. Chem. Soc.</u> 2000, Vol. 122, No. 46, pps. 11465-11472.	

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/LT/	C55	Ouyang, Jianyong et al., "Programmable Polymer Thin Film and Non-Volatile Memory Device", <i>Nature Publishing Group, Nature Materials</i> , Vol. 3, December 2004, pps. 918-922.
	C56	Hostetler, Michael J. et al., "Alkanethiolate Gold Cluster Molecules with Core Diameters from 1.5 to 5.2 nm: Core and Monolayer Properties as a Function of Core Size", <i>Langmuir</i> , 1998, Vol. 14, No. 1, pps. 17-30.
	C57	Ouyang, Jianyong et al., "Electric-Field-Induced Charge Transfer Between Gold Nanoparticle and Capping 2-Naphthalenethiol and Organic Memory Cells", <i>Applied Physics Letters</i> , 86, 2005, pps. 123507-1 to 123507-3.
	C58	Scheinert, S. et al., <i>J. Appl. Phys.</i> , 92 330 (2002)
	C59	Chiang, J.C., et al., <i>Synth. Met.</i> 13, 193, (1986). "Polyaniline: Protonic acid doping of the emeraldine form to the metallic regime."
	C60	Huang, J., et al., <i>J. Am. Chem. Soc.</i> , 25, 314 (2003) "Polyaniline Nanofibers: Facile Synthesis and Chemical Sensors"
	C61	Virji, S., et al. <i>Nano Lett.</i> , 4, 491 (2004). "Polyaniline Nanofiber Gas Sensors: Examiner of Response Mechanisms"
	C62	Huang, J., et al., <i>J. Am. Chem. Soc.</i> , 126, 851 (2004). "A General Chemical Route to Polyaniline Nanofibers"
	C63	Furukawa, T., <i>Adv. Colloid Interface Sci.</i> , 71-72, 183 (1997). "Structure and functional properties of ferroelectric polymer"
	C64	Tsuyoshi, T., et al., <i>App. Phys. Lett.</i> , 83, 4978 (2003). "Electrical carrier-injection and transport characteristics of photochromic diarylethene films"
	C65	Reed, M.A., et al., <i>Appl. Phys. Lett.</i> , 78, 3735 (2001). "Molecular random access memory cell"
	C66	Chen, Y., et al, <i>Appl. Phys. Lett.</i> 82, 1610 (2003). "Nanoscale molecular-switch devices fabricated by imprint lithography"
	C67	TANG, C.W. et al., "Organic Electroluminescent Diodes", <i>Appl. Phys. Lett.</i> 51 (12), September 21, 1987, p. 913-915.
	C68	FRIEND, R.H. et al., "Electroluminescence in Conjugated Polymers", <i>NATURE</i> , Vol. 397, January 14, 1999, p. 121-128.
	C69	SARICIFTCI, N.S. et al., "Photoinduced Electron Transfer from a Conducting Polymer to Buckminsterfullerene", <i>SCIENCE</i> , Vol. 258, November 27, 1992, p. 1474-1476.
	C70	GUNDLACH, D.J. et al., "Pentacene Organic Thin-Film Transistors-Molecular Ordering and Mobility", <i>IEEE ELECTRON DEVICE LETTERS</i> , Vol. 18, No. 3, March 1977, p. 87-89.
	C71	BALDO, Marc et al., "Organic Vapor Phase Deposition", <i>Adv. Mater.</i> 1998, 10, No. 18, p. 1505-1514.
	C72	CARCHANO, H. et al., "Bistable Electrical Switching in Polymer Thin Films", <i>APPLIED PHYSICS LETTERS</i> , Vol. 19, No. 19, November 15, 1971, p. 414-415.
	C73	XU, W. et al., "Two New All-Organic Complexes with Electrical Bistable States", <i>Appl. Phys. Lett.</i> 67 (15), October 9, 1995, p. 2241-2242.
	C74	MA, L.P. et al., "Data Storage with 0.7 nm Recording Marks on a Crystalline Organic Thin Film by a Scanning Tunneling Microscope", <i>APPLIED PHYSICS LETTERS</i> , Vol. 73, No. 6, August 10, 1998, p. 850-852.
↓	C75	HENISCH, H.K. et al., "Switching in Organic Polymer Films" <i>Applied Physics Letters</i> , Vol. 24, No. 12, June 15, 1974, p. 589-591.
/LT/	C76	BRYCE, Martin R., "Tetrathiafulvalenes as π -Electron Donors for Intramolecular Charge-Transfer Materials", <i>Advanced Materials</i> , 1999, 11, No. 1, p. 11-23.

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/LT/	C77	MARTIN, NAZARIO et al., "Evidence for Two Separate One-electron Transfer Events in Excited Fulleropyrrolidine Dyads Containing Tetrathiafulvalene (TTF)", <i>J. Phys. Chem. A</i> 2000, 104, p. 4648-4657.	<input type="checkbox"/>
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